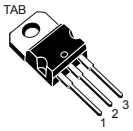
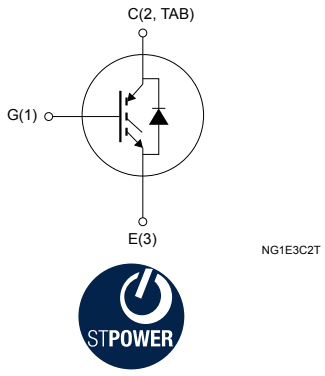
STGB14NC60KDT4, STGF14NC60KD, STGP14NC60KD

Datasheet

14 A, 600 V short-circuit rugged IGBT







Features

- Low on voltage drop ($V_{CE(sat)}$)
- Low C_{res} / C_{ies} ratio (no cross-conduction susceptibility)
- Very soft ultra-fast recovery antiparallel diode
- Short-circuit withstand time 10 µs

Applications

- High frequency inverters
- SMPS and PFC in both hard switch and resonant topologies
- Motor drives

Description

These devices are very fast IGBTs developed using advanced PowerMESH technology. This process guarantees an excellent trade-off between switching performance and low on-state behavior. These devices are well-suited for resonant or soft-switching applications.

Product status links
STGB14NC60KDT4
STGF14NC60KD
STGP14NC60KD

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D²PAK, TO-220	TO-220FP	
V_{CES}	Collector-emitter voltage (V_{GE} = 0 V)	600		V
I_C(1)	Continuous collector current at T_C = 25 °C	25	11	A
	Continuous collector current at T_C = 100 °C	14	7	
I_{CL}(2)	Turn-off latching current	50		A
I_{CP}(3)	Pulsed collector current	50		A
V_{GE}	Gate-emitter voltage	±20		V
I_F	Diode RMS forward current at T_C = 25 °C	20		A
I_{FSM}	Surge non repetitive forward current t_p = 10 ms sinusoidal	55		A
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T_C = 25 °C)		2.5	kV
t_{scw}	Short-circuit withstand time V_{CE} = 300 V, T_J = 125 °C, R_G = 10 Ω, V_{GE} = 12 V	10		µs
P_{TOT}	Total power dissipation at T_C = 25 °C	80	28	W
T_{stg}	Storage temperature range	-55 to 150		°C
T_J	Operating junction temperature range			°C

1. *Calculated according to the iterative formula:* $I_C(T_C) = \frac{T_{J(\max)} - T_C}{R_{thJC} \times V_{CE(sat)(\max)}\left(T_{J(\max)}, I_C(T_C)\right)}$
2. *V_{clamp} = 80% V_{CES}, T_J =150 °C, R_G = 10 Ω, V_{GE} = 15 V.*
3. *Pulse width limited by maximum junction temperature and turn-off within RBSOA.*

Table 2. Thermal data

Symbol	Parameter	Value		Unit
		D²PAK, TO-220	TO-220FP	
R_{thJC}	Thermal resistance, junction-to-case IGBT	1.56	4.5	°C/W
	Thermal resistance, junction-to-case diode	2.2	5.6	
R_{thJA}	Thermal resistance, junction-to-ambient	62.5		°C/W

2 Electrical characteristics

T_C = 25 °C unless otherwise specified

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	V_{GE} = 0 V, I_C = 1 mA	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15 V, I_C = 7 A		2.1	2.5	V
		V_{GE} = 15 V, I_C = 7 A, T_J = 125 °C		1.8		
$V_{GE(th)}$	Gate threshold voltage	V_{CE} = V_{GE}, I_C = 250 µA	4.5		6.5	V
I_{CES}	Collector cut-off current	V_{GE} = 0 V, V_{CE} = 600 V			0.15	mA
		V_{GE} = 0 V, V_{CE} = 600 V, T_J = 125 °C (1)			1	
I_{GES}	Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = ±20 V			±100	nA
g_{fs} (2)	Forward transconductance	V_{CE} = 15 V, I_C = 7 A		3.2		S

1. *Specified by design, not tested in production.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	V_{CE} = 25 V, f = 1 MHz, V_{GE} = 0 V	-	760	-	pF
C_{oes}	Output capacitance		-	86	-	pF
C_{res}	Reverse transfer capacitance		-	15.5	-	pF
Q_g	Total gate charge	V_{CC} = 390 V, I_C = 7 A, V_{GE} = 0 to 15 V (see Figure 19. Gate charge test circuit)	-	34.4	-	nC
Q_{ge}	Gate-emitter charge		-	8.1	-	nC
Q_{gc}	Gate-collector charge		-	16.4	-	nC

Table 5. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{CC} = 390 V, I_C = 7 A,	-	22.5	-	ns
t_r	Current rise time	R_G = 10 Ω, V_{GE} = 15 V	-	8.5	-	ns
$(di/dt)_{on}$	Turn-on current slope	(see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	700	-	A/µs
$t_{d(on)}$	Turn-on delay time	V_{CC} = 390 V, I_C = 7 A,	-	22	-	ns
t_r	Current rise time	R_G = 10 Ω, V_{GE} = 15 V, T_J = 125 °C	-	9.5	-	ns
$(di/dt)_{on}$	Turn-on current slope	(see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	680	-	A/µs
$t_r(V_{off})$	Off voltage rise time	V_{CC} = 390 V, I_C = 7 A,	-	60	-	ns
$t_{d(off)}$	Turn-off delay time	R_G = 10 Ω, V_{GE} = 15 V	-	116	-	ns
t_f	Current fall time	(see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	75	-	ns
$t_r(V_{off})$	Off voltage rise time	V_{CC} = 390 V, I_C = 7 A,	-	24	-	ns
$t_{d(off)}$	Turn-off delay time	R_G = 10 Ω, V_{GE} = 15 V, T_J = 125 °C	-	196	-	ns
t_f	Current fall time	(see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	144	-	ns

Table 6. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on} (1)	Turn-on switching energy	V_{CE} = 390 V, I_C = 7 A,	-	82	-	µJ
E_{off} (2)	Turn-off switching energy	R_G = 10 Ω, V_{GE} = 15 V	-	155	-	µJ
E_{ts}	Total switching energy	(see Figure 17. Test circuit for inductive load switching	-	237	-	µJ
E_{on} (1)	Turn-on switching energy	V_{CE} = 390 V, I_C = 7 A,	-	131	-	µJ
E_{off} (2)	Turn-off switching energy	R_G = 10 Ω, V_{GE} = 15 V, T_J = 125 °C	-	370	-	µJ
E_{ts}	Total switching energy	(see Figure 17. Test circuit for inductive load switching	-	501	-	µJ

1. *Including the reverse recovery of the diode.*
2. *Including the tail of the collector current.*

Table 7. Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on-voltage	I_F = 7 A	-	1.8	2.1	V
		I_F = 7 A, T_J = 125 °C	-	1.3		
t_{rr}	Reverse recovery time	I_F = 5 A, V_R = 40 V, di/dt = 100 A/µs (see Figure 18. Diode reverse recovery waveform)	-	37		ns
Q_{rr}	Reverse recovery charge		-	40		nC
I_{rrm}	Reverse recovery current		-	2.1		A
t_{rr}	Reverse recovery time	I_F = 7 A, V_R = 40 V, di/dt = 100 A/µs, T_J = 125 °C (see Figure 18. Diode reverse recovery waveform)	-	61		ns
Qrr	Reverse recovery charge		-	98		nC
I_{rr}	Reverse recovery current		-	3.2		A

2.1 Electrical characteristics (curves)

Figure 1. Typical output characteristics

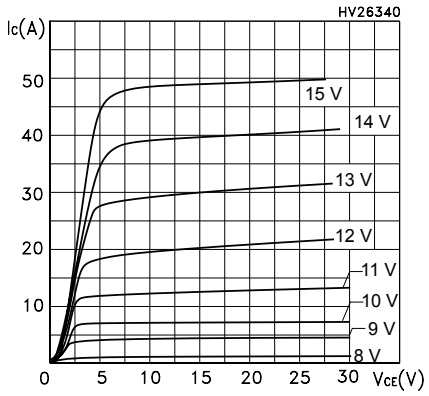


Figure 2. Typical transfer characteristics

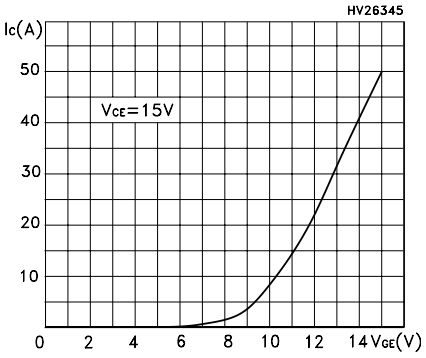


Figure 3. Typical transconductance characteristics

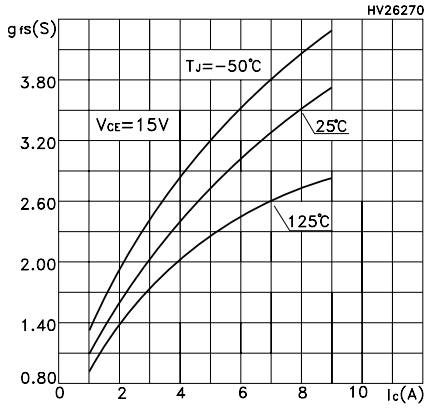


Figure 4. Typical collector-emitter on voltage vs temperature

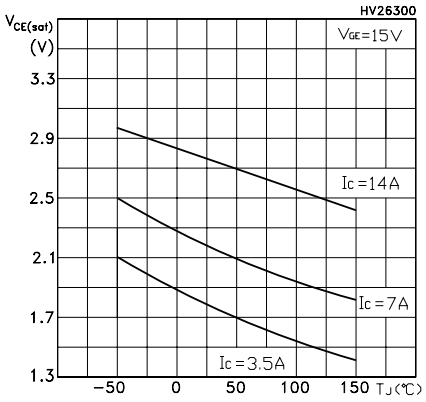


Figure 5. Typical gate charge characteristics

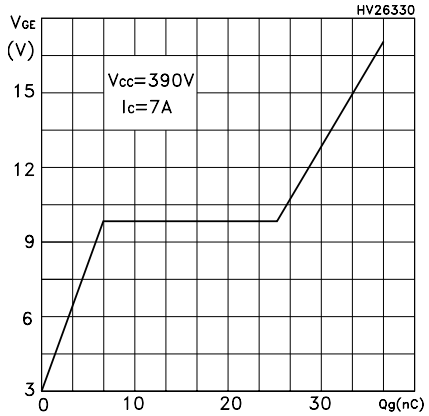


Figure 6. Typical capacitance characteristics

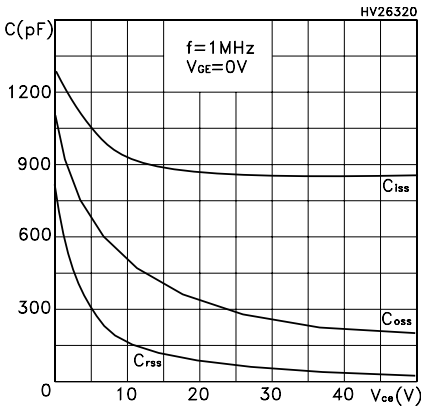


Figure 7. Normalized gate threshold vs temperature

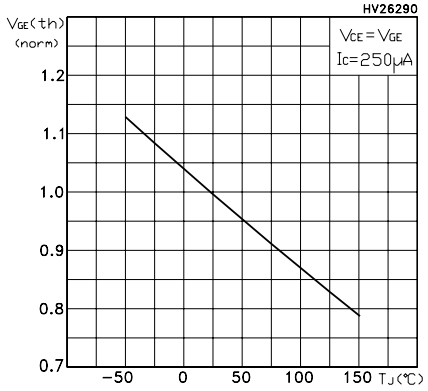


Figure 8. Typical collector-emitter on voltage vs collector current

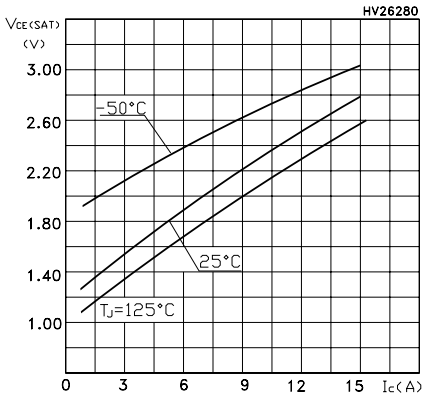


Figure 9. Normalized breakdown voltage vs temperature

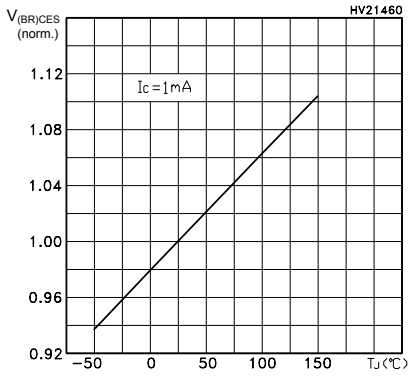


Figure 10. Typical switching energy vs temperature

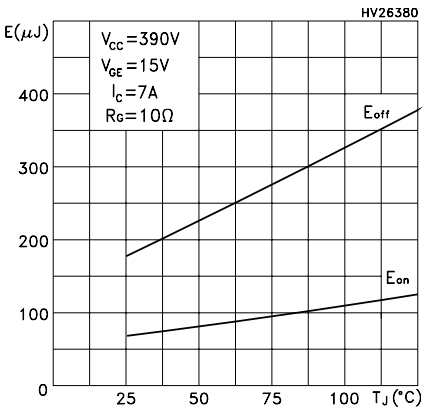


Figure 11. Typical switching energy vs gate resistance

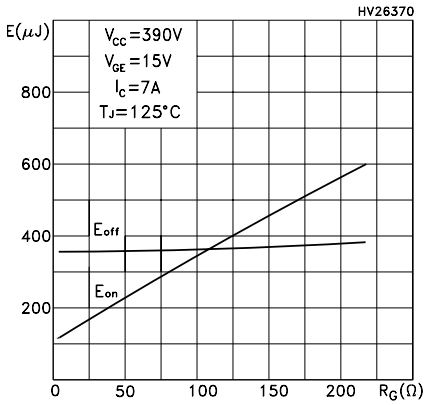


Figure 12. Typical switching energy vs collector current

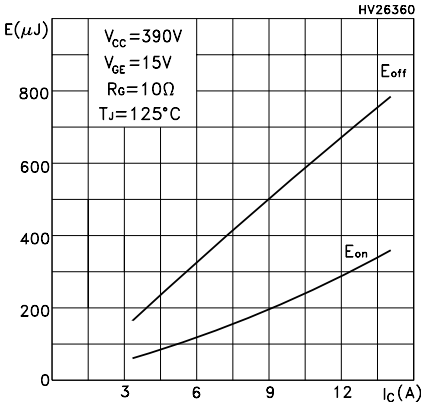


Figure 13. Reverse bias safe operating area

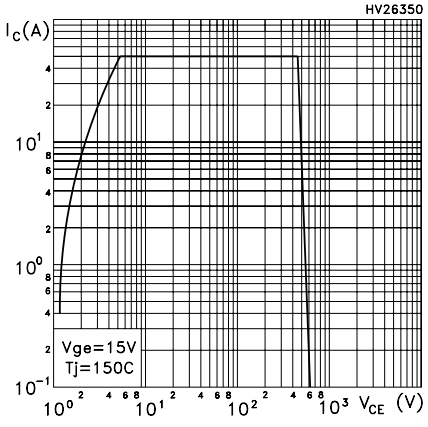


Figure 14. Normalized transient thermal impedance for D²PAK and TO-220

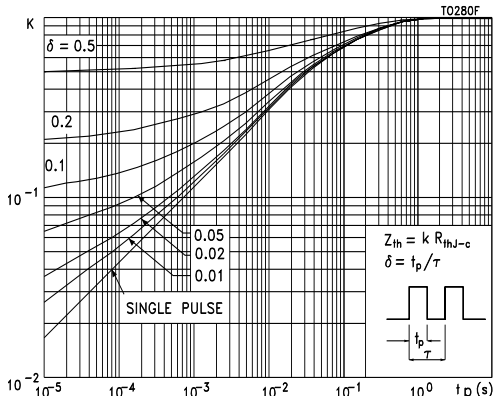


Figure 15. Normalized transient thermal impedance for TO-220FP

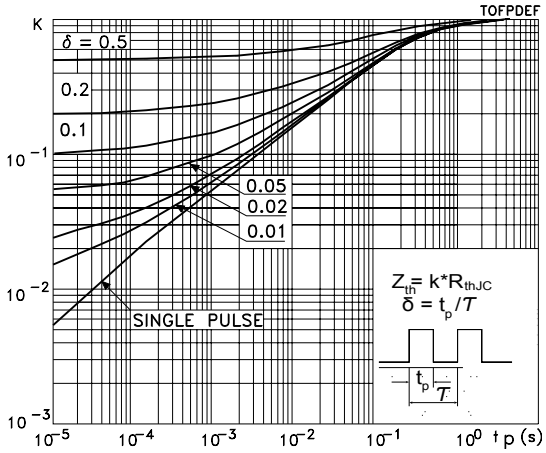
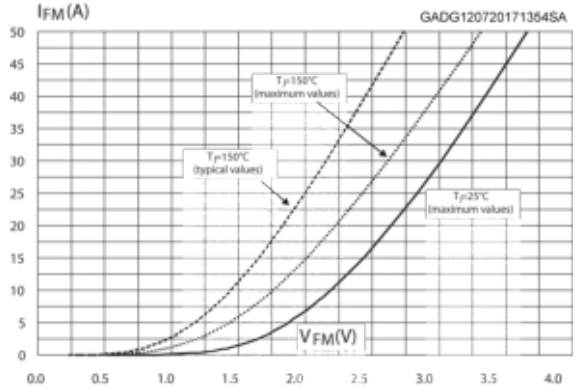


Figure 16. Typical emitter-collector diode characteristics



3 Test circuits

Figure 17. Test circuit for inductive load switching

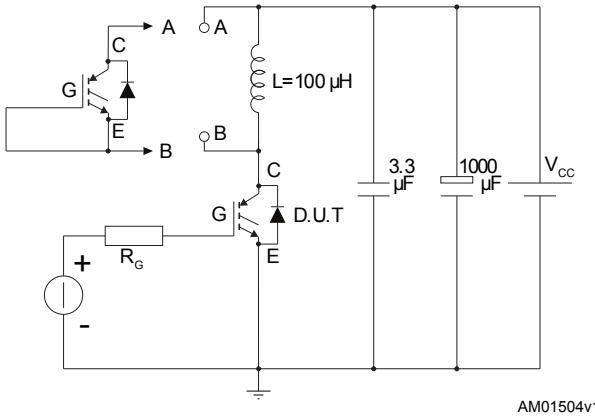


Figure 18. Diode reverse recovery waveform

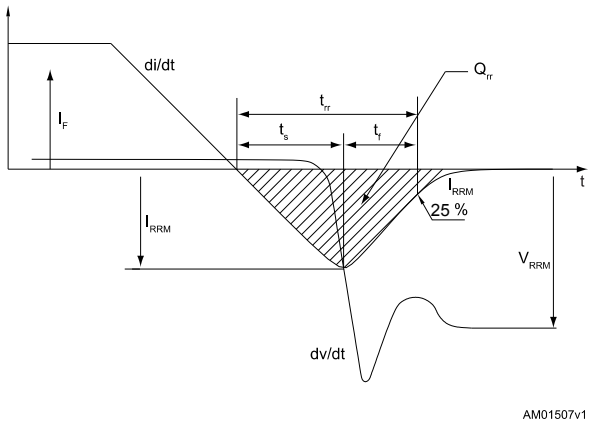


Figure 19. Gate charge test circuit

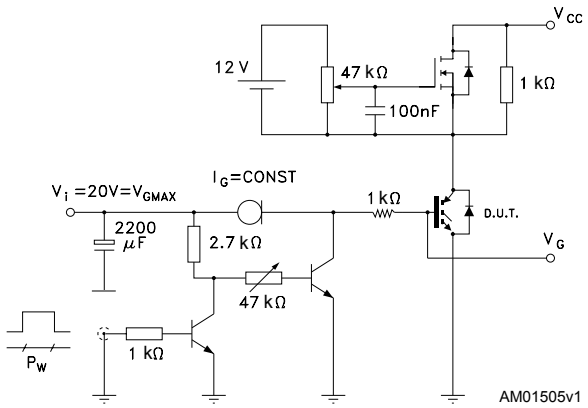
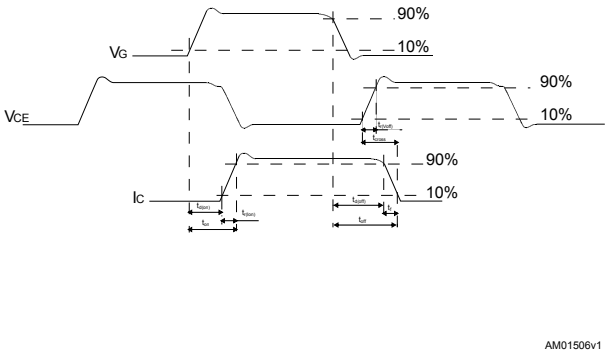


Figure 20. Switching waveform



4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK (TO-263) type A package information

Figure 21. **D²PAK (TO-263) type A package outline**

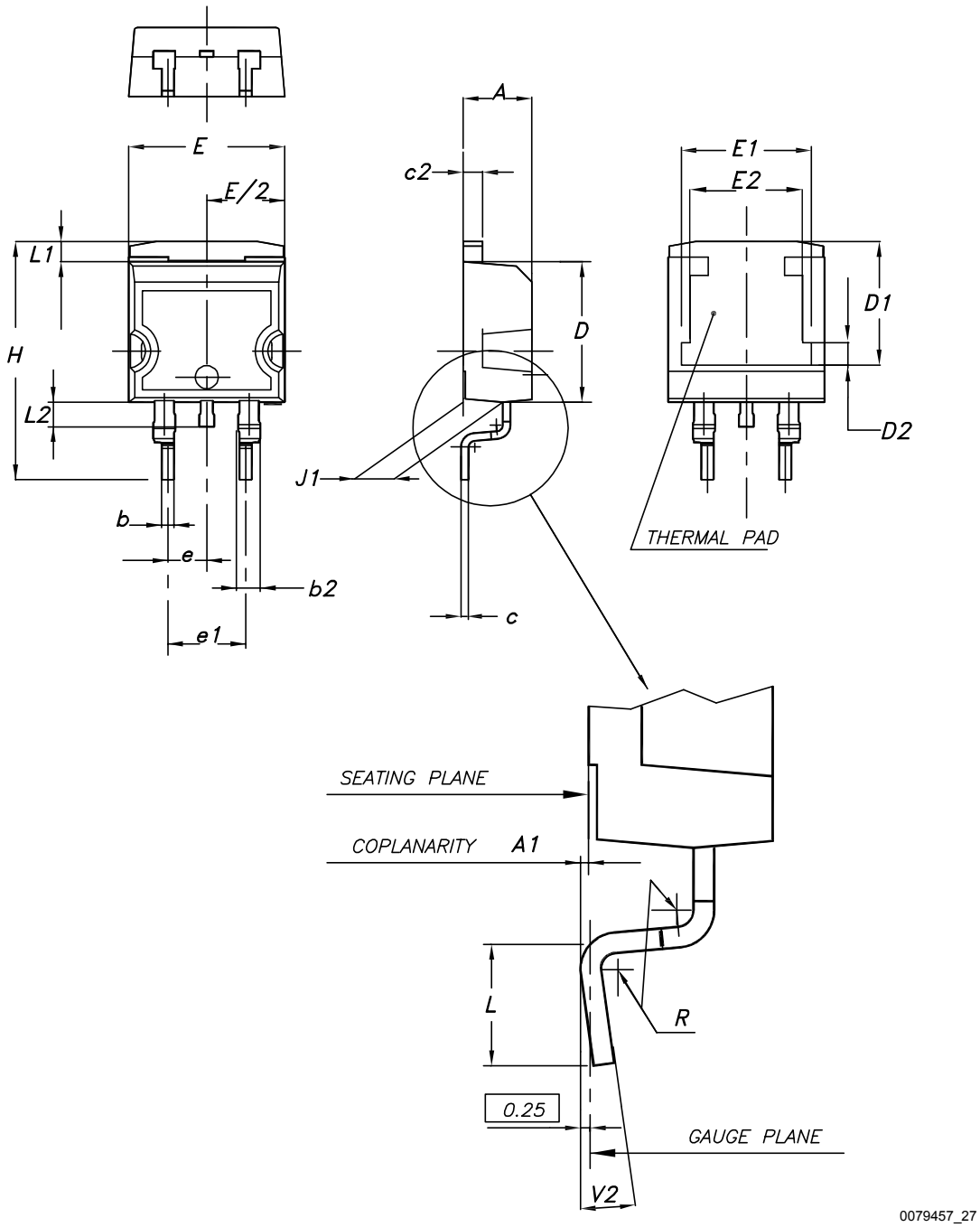
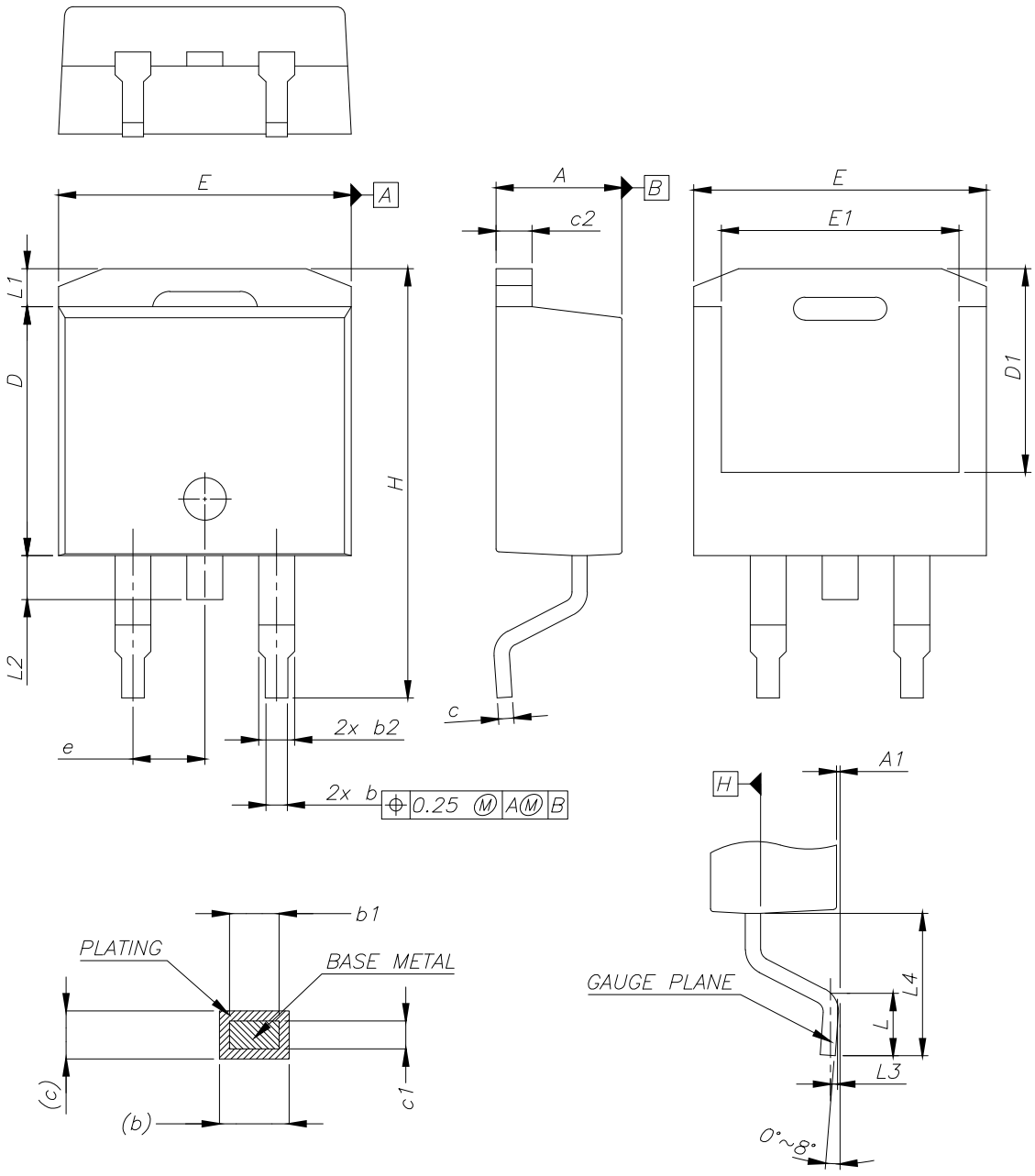


Table 8. **D²PAK (TO-263) type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

4.2 D²PAK (TO-263) type B package information

Figure 22. **D²PAK (TO-263) type B package outline**

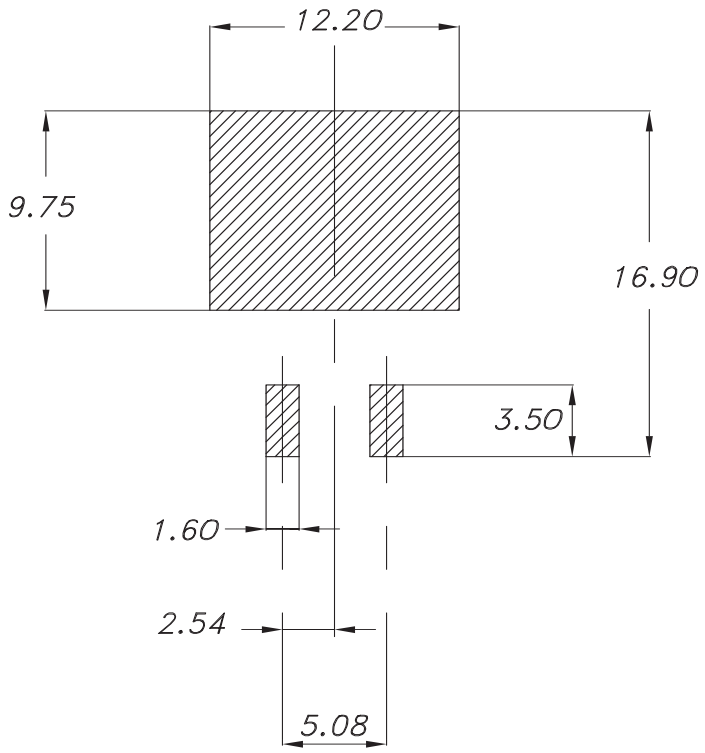


0079457_27_B

Table 9. **D²PAK (TO-263) type B mechanical data**

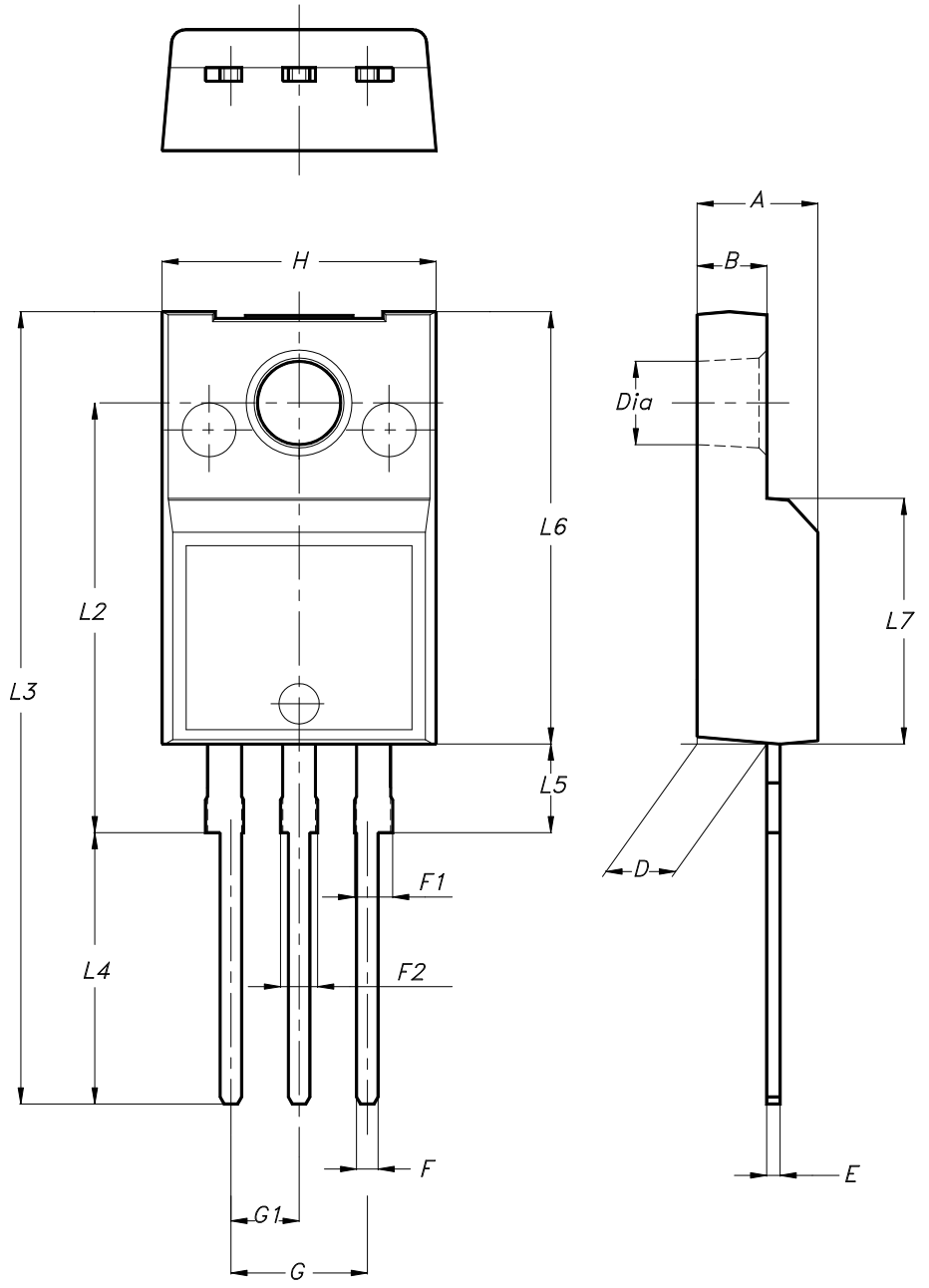
Dim.	mm		
	Min.	Typ.	Max.
A	4.36		4.56
A1	0.00		0.25
b	0.70		0.90
b1	0.51		0.89
b2	1.17		1.37
c	0.38		0.694
c1	0.38		0.534
c2	1.19		1.34
D	8.60		9.00
D1	6.90		7.50
E	10.15		10.55
E1	8.10		8.70
e	2.54 BSC		
H	15.00		15.60
L	1.90		2.50
L1			1.65
L2			1.78
L3		0.25	
L4	4.78		5.28

Figure 23. **D²PAK (TO-263) recommended footprint (dimensions are in mm)**



4.3 TO-220FP type B package information

Figure 24. **TO-220FP type B package outline**



7012510_B_rev.14

Table 10. **TO-220FP type B package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

4.4 TO-220 type A package information

Figure 25. **TO-220 type A package outline**

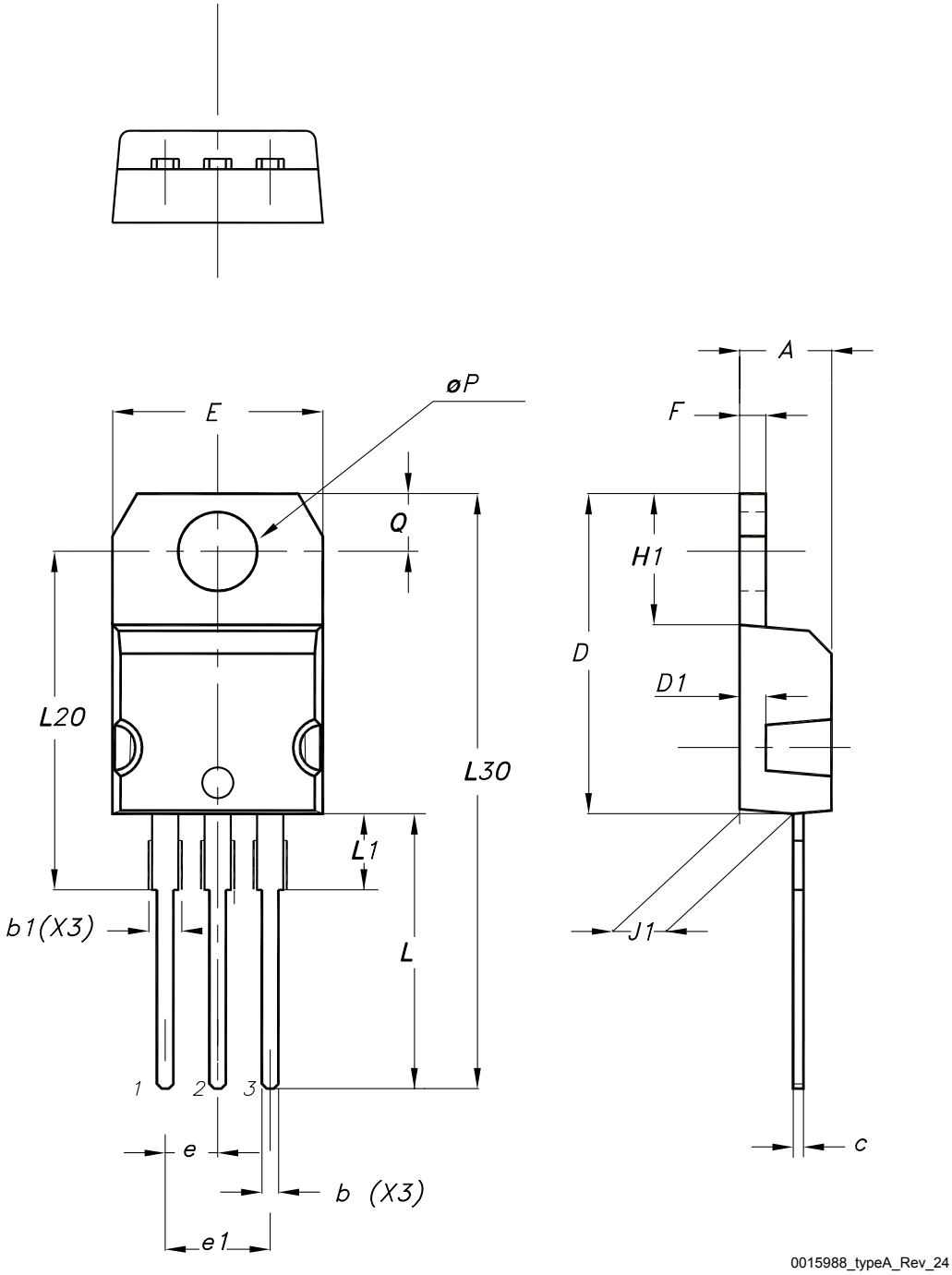
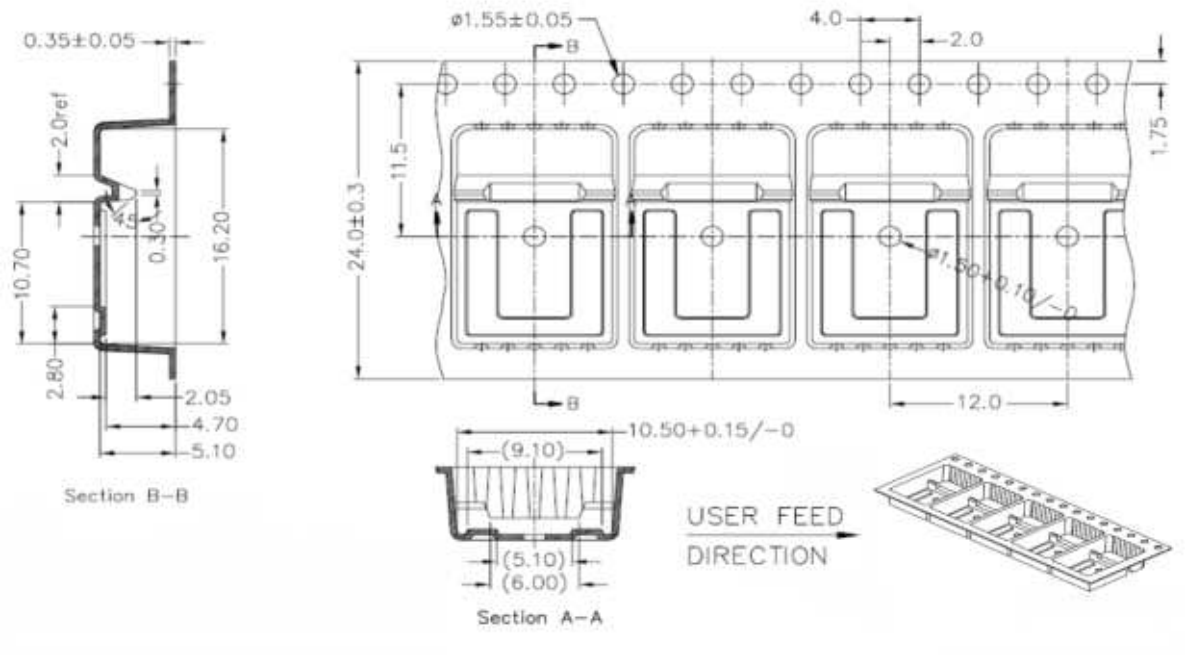


Table 11. **TO-220 type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

4.5 D²PAK packing information

Figure 26. **D²PAK tape drawing (dimensions are in mm)**



DM01095771_1

5 Ordering information

Table 12. **Order codes**

Order codes	Marking	Package	Packing
STGB14NC60KDT4	GB14NC60KD	D²PAK	Tape and reel
STGF14NC60KD	GF14NC60KD	TO-220FP	Tube
STGP14NC60KD	GP14NC60KD	TO-220	

Revision history

Table 13. **Document revision history**

Date	Revision	Changes
14-Jun-2005	1	New release
05-Jul-2005	2	Complete version
22-Jul-2005	3	Value changed in table 6
27-Jan-2006	4	Inserted ecopack indication
28-Apr-2006	5	New template, modified curves 6 and 8
02-Apr-2008	6	Modified test conditions on Table 4
15-Mar-2010	7	Updated packages mechanical data.
12-Jul-2017	8	Modified *Table 6: "Switching on/off (inductive load)"*, *Table 7: "Switching energy (inductive load)"* and *Table 8: "Collector-emitter diode"*. Updated *Section 4: "Package information"*.
14-May-2025	9	Updated Section 4: Package information.

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